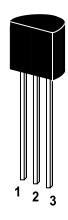
NPN Silicon Epitaxial Planar Transistor

These transistors are subdivided into three groups A, B and C according to their current gain. The type BC546 is available in groups A and B, however, the types BC547 and BC548 can be supplied in all three groups. The BC549 is low-noise type and available in groups B and C. As complementary types, the PNP transistors BC556...BC559 are recommended.

On special request, these transistors can be manufactured in different pin configurations.



1. Collector 2. Base 3. Emitter

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25$ °C)

		Symbol	Value	Unit
Collector Base Voltage	ST BC546	V_{CBO}	80	V
	ST BC547	V_{CBO}	50	V
	ST BC548, ST BC549	V_{CBO}	30	V
Collector Emitter Voltage	ST BC546	V _{CES}	85	V
	ST BC547	V _{CES}	50	V
	ST BC548, ST BC549	V _{CES}	30	V
Collector Emitter Voltage	ST BC546	V _{CEO}	65	V
	ST BC547	V_{CEO}	45	V
	ST BC548, ST BC549	V_{CEO}	30	V
Emitter Base Voltage	ST BC546, ST BC547	V _{EBO}	6	V
	ST BC548, ST BC549	V_{EBO}	5	V
Collector Current		I _C	100	mA
Peak Collector Current		I _{CM}	200	mA
Peak Base Current		I _{BM}	200	mA
Peak Emitter Current		-I _{EM}	200	mA
Power Dissipation		P _{tot}	500 ¹⁾	mW
Junction Temperature		T _j	150	οС
Storage Temperature Range		Ts	-65 to +150	°С
1) Valid provided that leads a	re kept at ambient temperati	ure at a distand	ce of 2 mm from case	



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)







ST BC546 ... BC549

Characteristics at T_{amb}=25 °C

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain.						
at V _{CE} =5V, I _C =10μA	Current Gain Group A	h _{FE}	-	90	-	-
	В	h _{FE}	-	150	-	-
	С	h _{FE}	-	270	-	-
at V _{CE} =5V, I _C =2mA	Current Gain Group A	h _{FE}	110	180	220	-
	В	h _{FE}	200	290	450	-
	С	h _{FE}	420	500	800	-
at V_{CE} =5V, I_{C} =100mA	Current Gain Group A	h _{FE}	-	120	-	-
	В	h _{FE}	-	200	-	-
	С	h _{FE}	-	400	-	-
Collector Saturation Voltage	•					
at I _C =10mA, I _B =0.5mA		V_{CEsat}	-	80	200	mV
at I _C =100mA, I _B =5mA		V_{CEsat}	-	200	600	mV
Base Saturation Voltage						
at $I_C=10$ mA, $I_B=0.5$ mA		V_{BEsat}	-	700	-	mV
at I _C =100mA, I _B =5mA		V_{BEsat}	-	900	-	mV
Base Emitter Voltage						
at V_{CE} =5V, I_{C} =2mA		V_{BE}	580	660	700	mV
at V_{CE} =5V, I_{C} =10mA		V_{BE}	-	-	720	mV
Collector Emitter Cutoff Cur	rent					
at V _{CE} =80V	ST BC546	I _{CES}	-	0.2	15	nA
at V _{CE} =50V	ST BC547	I _{CES}	-	0.2	15	nA
at V _{CE} =30V	ST BC548, ST BC549	I _{CES}	-	0.2	15	nA
at $V_{CE}=80V$, $T_j=125$ $^{\circ}C$	ST BC546	I _{CES}	-	-	4	μΑ
at V_{CE} =50V, T_j =125 $^{\circ}$ C	ST BC547	I _{CES}	-	-	4	μΑ
Thermal Resistance Junction to Ambient Air		R _{thA}	-	-	250 ¹⁾	K/W
1) Valid provided that leads a	are kept at ambient temperati	re at a dist	ance of 2 n	nm from cas	se	

Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case

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ST BC546 ... BC549

Characteristics at T_{amb}=25 °C

		Symbol	Min.	Тур.	Max.	Unit
at V _{CE} =30V, T _j =125 ^O C	ST BC548, ST BC549	I _{CES}	-	-	4	μΑ
					4	μΑ
Gain Bandwidth Product						
at V _{CE} =5V, I _C =10mA, f=100MHz		f _T	-	300	-	MHz
Collector Base Capacitance						
at V _{CB} =10V, f=1MHz		C_{CBO}	-	3.5	6	pF
Emitter Base Capacitance						
at V _{EB} =0.5V, f=1MHz		C_{EBO}	-	9	-	pF
Noise Figure						
at V_{CE} =5V, I_{C} =200 μ A, R_{G} =2k Ω , f=1kHz, Δ f=200Hz						
	ST BC546, ST BC547	F	-	2	10	dB
	ST BC548, STBC549	F	-	1.2	4	dB







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